

**•General Description**

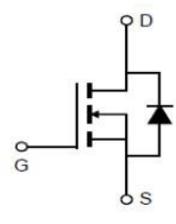
The SJ MOSFET LH60R028FD has the low  $R_{DS(on)}$ , low gate charge, fast switching and excellent avalanche characteristics. This device offers extremely fast and robust body diode, and is suitable for telecom and power supplies

**•Features**

- 100% Avalanche Tested
- Low Power Loss By High Speed Switching
- Low On-Resistance

**•Application**

- DC-DC Converter
- UPS-Micro Inverter System
- PFC Power Supply

	$V_{DS}=600V$ $R_{DS(ON)}=0.028\Omega$ $I_D=82A$
	<b>■RoHS COMPLIANT</b>
<b>TO-247</b>	

**•Ordering Information:**

Part number	LH60R028FD
Package	TO-247
Basic ordering unit (pcs)	330
Normal Package Material Ordering Code	LH60R028FDT2-T0247-TU
Halogen Free Ordering Code	LH60R028FDT2-T0247-TU-HF

**•Absolute Maximum Ratings (TC =25°C)**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	600	V
Gate-Source Voltage	$V_{GS}$	±30	V
Continuous Drain Current	$I_D$ $T_C = 25^\circ C$	82	A
	$I_D$ $T_C = 100^\circ C$	48	
Pulsed drain current ( $T_C = 25^\circ C$ , $t_p$ limited by $T_{imax}$ ) <sup>1</sup>	$I_D$ pulse	246	A
Power Dissipation( $T_C=25^\circ C$ )	$P_D$	480	W
Single Pulse Avalanche Energy <sup>2</sup>	$E_{AS}$	2190	mJ
Diode dv/dt ruggedness	dv/dt	50	V/ns
Operating Junction Temperature	$T_J$	-55~+150	°C
Storage Temperature	$T_{STG}$	-55~+150	°C

**●Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	$B_{V_{DS}}$	$V_{GS}=0V, I_D=250\mu A$	600	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	3.0	-	5.0	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=600V, V_{GS}=0V,$ $T_J=25^\circ C$ $T_J=150^\circ C$	-	-	1	$\mu A$
			-	-	100	$\mu A$
Gate- Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 30V, V_{DS}=0V$	-	-	$\pm 100$	nA
Drain-Source On State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$	-	0.028	0.03	$\Omega$
Gate Resistance	$R_G$	$V_{GS}=0V, f=1.0MHz$	-	3.8	-	$\Omega$

**●Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	$C_{iss}$	$V_{GS}=0V, V_{DS}=25V$  $F=1MHz$	-	6380	-	pF
Output capacitance	$C_{oss}$		-	98	-	
Reverse transfer capacitance	$C_{rss}$		-	184	-	
Turn -Off Delay Time	$T_{d(off)}$	$V_{DD}=300V,$ $I_D=53A, R_G=25\Omega$	-	120	-	ns
Turn-on delay time	$T_{d(on)}$		-	106	-	
Rise time	$T_r$		-	95	-	
Fall time	$T_f$		-	11	-	
Total Gate Charge	$Q_g$	$I_D=60A, V_{DS}=480V$  $V_{GS}=10V$	-	162	-	nC
Gate-to-Source Charge	$Q_{gs}$		-	38	-	
Gate-to-Drain Charge	$Q_{gd}$		-	48	-	
Diode Forward Voltage	$V_{SD}$	$I_D=20A$ $V_{GS}=0V$	-	-	1.4	V
Body Diode Reverse Recovery Time	$T_{rr}$	$I_D=20A,$ $V_{ds}=520V$	-	280	-	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	8.56	-	$\mu C$
Peak Reverse Recovery Current	$I_{rrm}$		-	48	-	A

**●Thermal Characteristics**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$	-	0.32	-	$^\circ C/W$
Thermal resistance, junction - ambient	$R_{thJA}$	-	62.5	-	$^\circ C/W$

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $I_{AS}=25A, V_{DD}=50V, R_G=25\Omega, \text{Starting } T_J=25^\circ C$

•Typical Characteristics

Figure 1. Output Characteristics

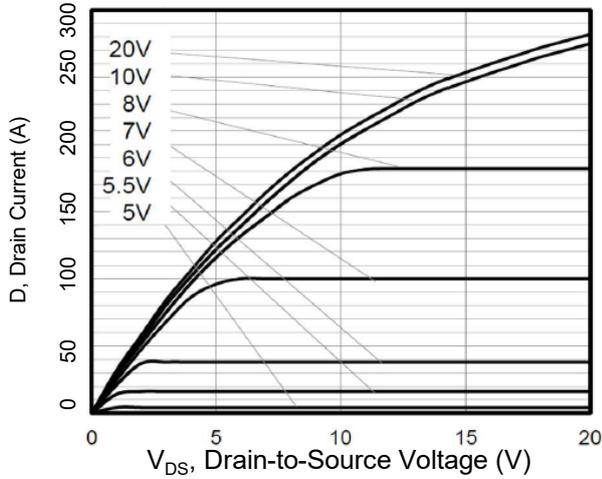


Figure 2. Transfer Characteristics

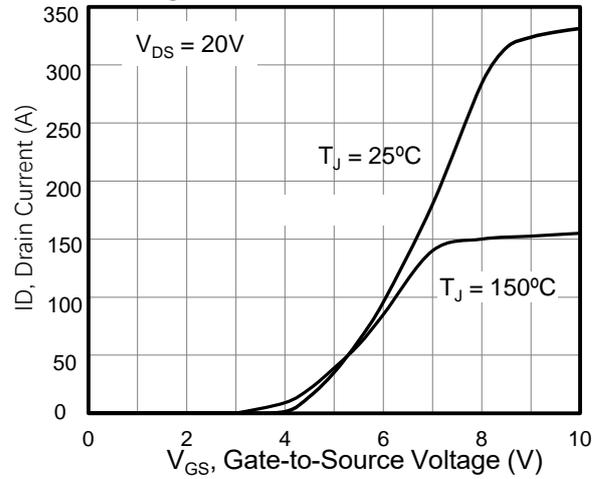


Figure 3. On-Resistance vs. Drain Current

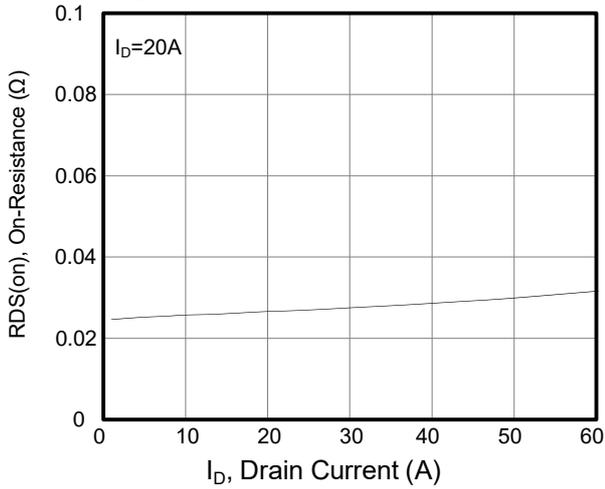


Figure 4. Capacitance

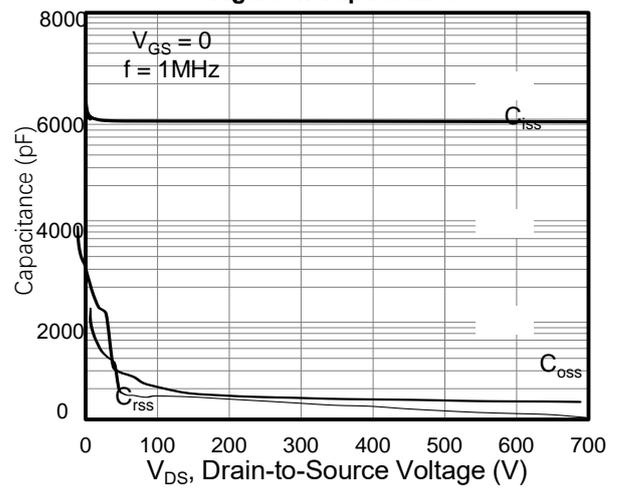


Figure 5. Gate Charge

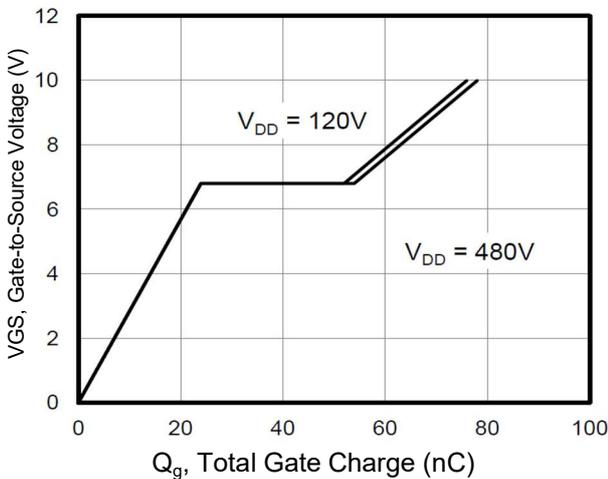
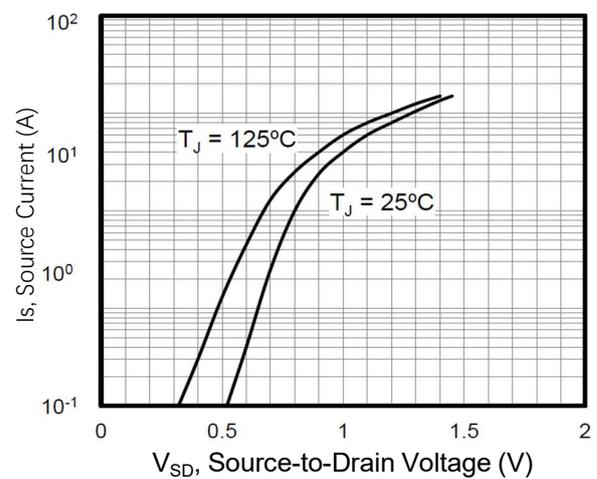
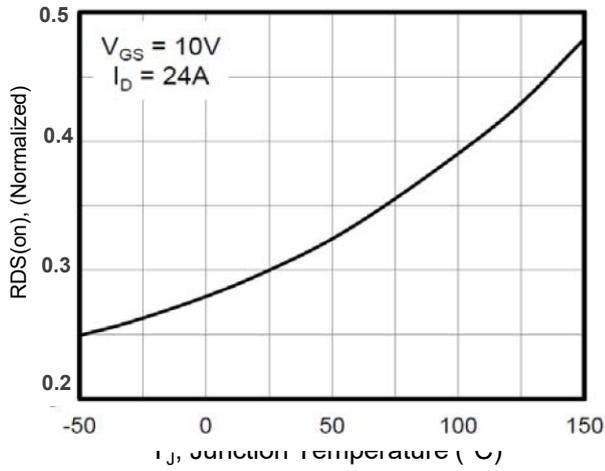


Figure 6. Body Diode Forward Voltage

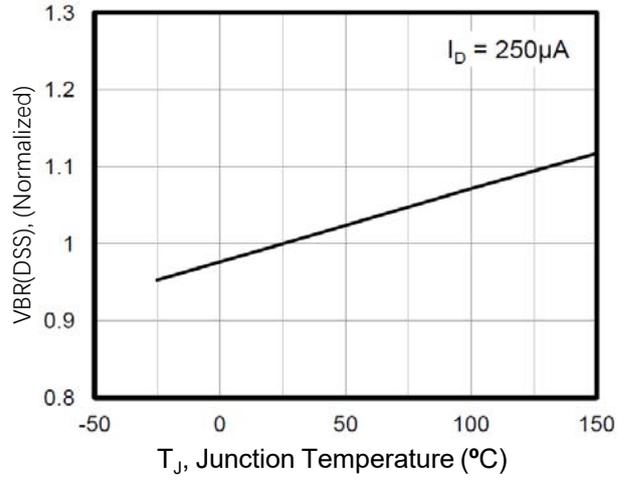


• **Typical Characteristics (cont.)**

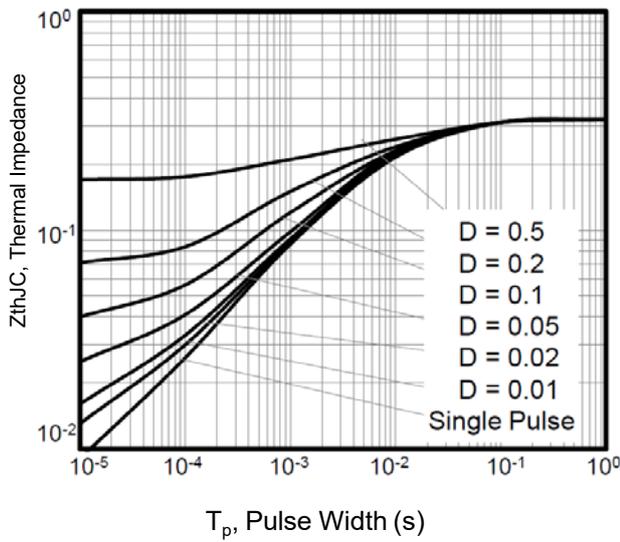
**Figure 7. On-Resistance vs. Junction Temperature**



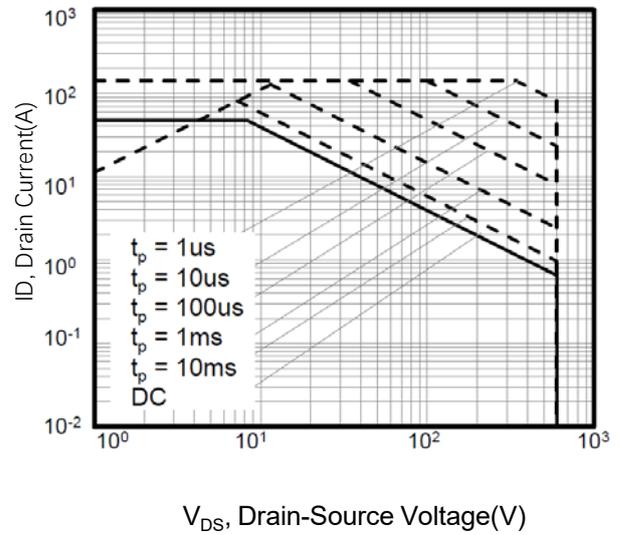
**Figure 8. Breakdown voltage vs. Junction Temperature**



**Figure 9. Transient Thermal Impedance for TO-247**



**Figure 10. Safe operation area for TO-247**



● Test Circuits & Waveforms

Figure 11. Gate Charge Test Circuit and Waveform

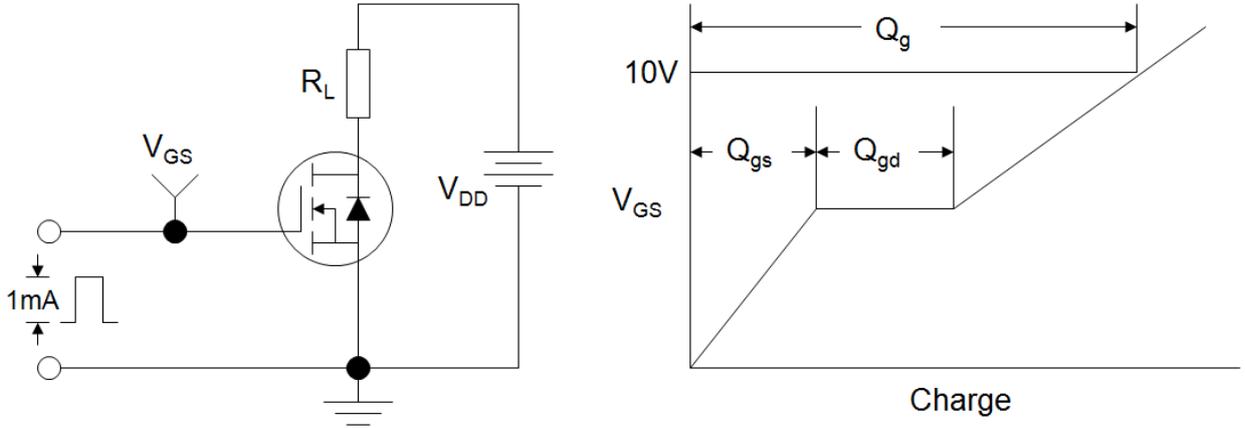


Figure 12. Resistive Switching Test Circuit and Waveform

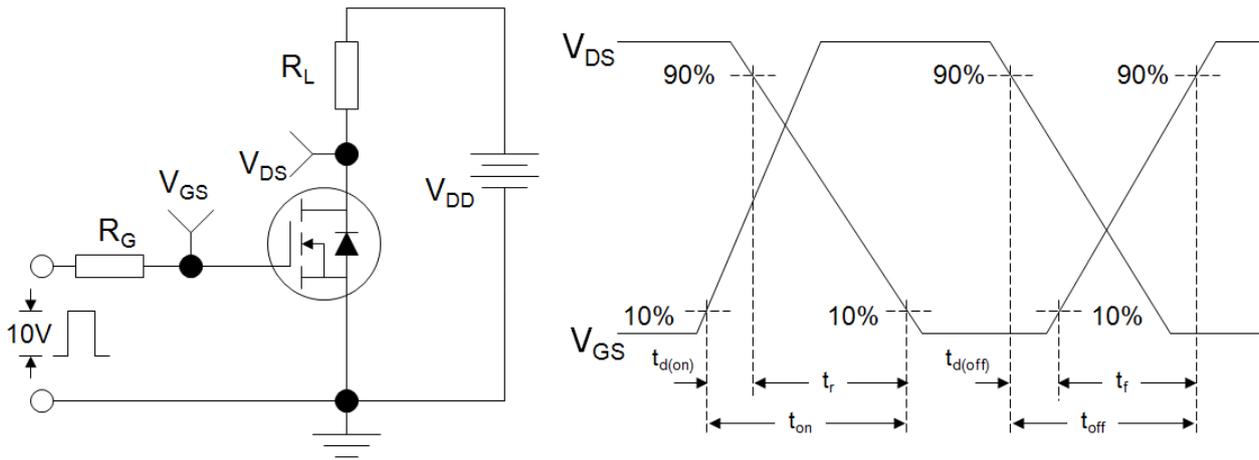
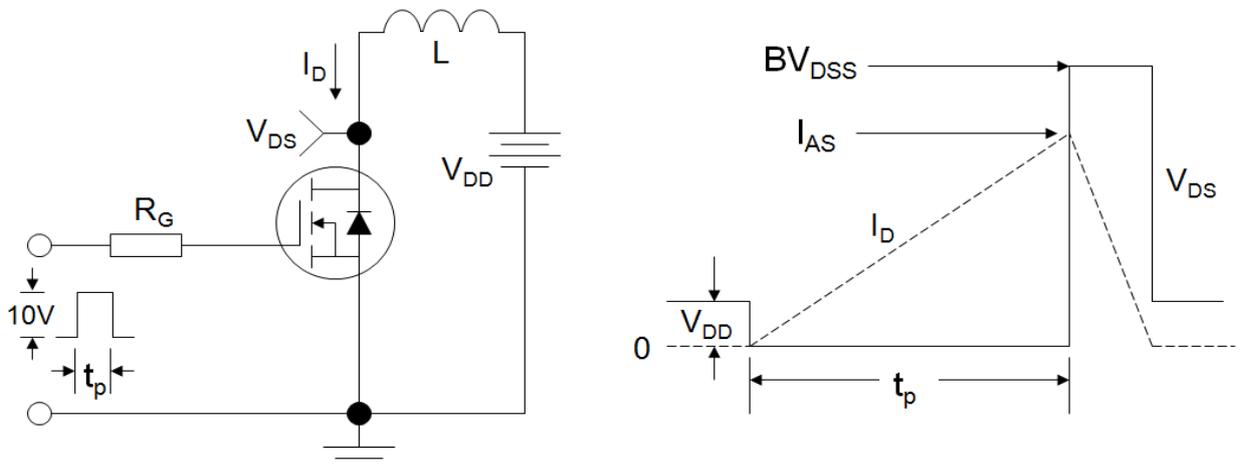


Figure 13. Unclamped Inductive Switching Test Circuit and Waveform



●Dimensions (TO-247)

UNIT:mm

SYMBOL	min	max	SYMBOL	min	max
A	15.60	16.00	G2	1.95	2.25
B	20.80	21.20	N	5.25	5.65
C	4.85	5.15	L1	4.00	4.30
D	1.85	2.15	L	19.60	20.40
E	1.00	1.40	I	2.30	2.50
F	0.50	0.70	ΦP	3.30	3.70
G1	3.00	3.30			

